BC817 / BC818

NPN Silicon Epitaxial Planar Transistors

for switching, AF driver and amplifier application,

These transistors are subdivided into three groups -16, -25, -40 according to their current gain. As complementary types, the PNP transistors BC807 and BC808 are recommended.



1. Base 2. Emitter 3. Collector SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit	
Collector Base Voltage	BC817 BC818	V _{CBO}	50 30	V	
Collector Emitter Voltage	BC817 BC818	V _{CEO}	45 25	V	
Emitter Base Voltage		V _{EBO}	5	V	
Collector Current		Ι _C	500	mA	
Power Dissipation		P _{tot}	200	mW	
Thermal Resistance, Junction to Ambient		$R_{ ext{ heta}JA}$	500	K/W	
Junction Temperature		TJ	150	°C	
Storage Temperature Range		Ts	- 55 to + 150	°C	

Electrical Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Тур.	Max.	Unit	
DC Current Gain							
at $V_{CE} = 1 \text{ V}$, $I_{C} = 100 \text{ mA}$	Current Gain Group	-16	h _{FE}	100	-	250	-
		-25	h _{FE}	160	-	400	-
		-40	h _{FE}	250	-	600	-
at $V_{CE} = 1 \text{ V}, I_C = 500 \text{ mA}$			h _{FE}	40	-	-	-
Collector Base Cutoff Current			1			100	ب م
at $V_{CB} = 20 V$			ICBO	-	-	100	ΠA
Emitter-Base Cutoff Current						100	n۸
at V _{EB} = 5 V			IEBO	-	-	100	ΠA
Collector Saturation Voltage			V			0.7	V
at $I_{C} = 500 \text{ mA}$, $I_{B} = 50 \text{ mA}$			V CEsat	-	-	0.7	V
Base-Emitter Voltage			V			1.2	V
at $I_C = 500 \text{ mA}$, $V_{CE} = 1 \text{ V}$			V BE(on)	-	-	1.2	V
Gain -Bandwidth Product			£	100			
at $V_{CE} = 5 V$, $I_C = 10 mA$, $f = 50$	MHz		ΙŢ	100	-	-	IVITZ
Collector-Base Capacitance			0		Б		nΕ
at V_{CB} = 10 V, f = 1 MHz			CCBO	-	5	-	μг







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